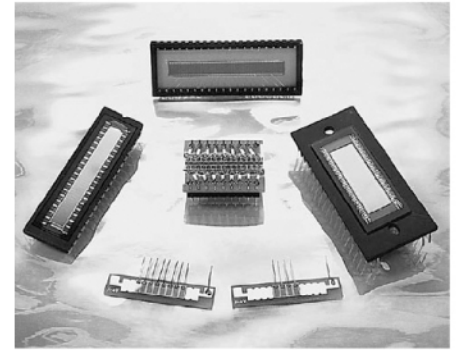


Features

- Common Substrate Array
- Ultra Low Cross Talk
- UV Enhanced (A5V-35UV)
- Low Dark Current
- Low Capacitance
- Solderable

Applications

- Level Meters
- Optical Spectroscopy
- Medical Equipment
- High Speed Photometry
- Computed Tomography Scanners
- Position Sensors



Model Number	Number of Elements	Active Area Per Element		Pitch (mm)	Responsivity (A/W)	Shunt Resistance (MΩ)	Dark Current (pF)	Capacitance (pF)		NEP (W/√Hz)		Temp.* Range (°C)		Package Style
		Area (mm ²)	Dimensions (mm)		970 nm	-10 mV	-10 V	0 V	-10 V	0V 970nm	-10mV 970nm	Operating	Storage	
					typ.	typ.	typ.	typ.	min.	typ.				

Photoconductive Arrays

A5C-35	35	3.9	4.39 x 0.89	0.99	0.65	-	0.05	-	12	-	6.2 e-15	-30 ~ +85	-40 ~ +125	Pin DIP
A5C-38	38													PCB

Photovoltaic Arrays

A2V-16	16	1.92	1.57 x 1.22	1.59	0.60	1000	-	170	-	4.8 e-15	-	-30 ~ +85	-40 ~ +125	PCB
A2V-35	35	3.9	4.39 x 0.89	0.99	0.60	1000	-	340	-	4.8 e-15	-			Pin DIP
A3V-38	38													Ceramic
A2V-76	76	1.8	6.45 x 0.28	0.31	0.50	500	-	160	-	8.2 e-15	-			Pin DIP

UV Enhanced Array (All Specifications @ λ=254nm, V_{BIAS} = -10V)

A5V-35UV	35	3.9	4.39 x 0.89	0.99	0.06**	500	-	340	-	6.8 e-14	-			Pin DIP
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Model Number	Number of Elements	Element Size		Active Area per Element	Pitch	Responsivity (A/W)	Open Circuit Voltage / Element (mV)	Shunt Resistance (MΩ)	Capacitance (pF)
		mm (inches)	mm ² (inches ²)	mm ² (inches ²)	mm (inches)	970 nm	10mW / cm ² 2850 °K	-10 mV	0 V
						typ.	typ.	typ.	typ.

Monolithic Solderable Chip Arrays (Typical Electro-Optical Specifications at T_A = 23°C)

A4V-2	2	1.52 x 2.79 (0.06 x 0.110)	4.24 (0.007)	1.90 (0.075)	0.6	500	1000	500
A4V-4	4							
A4V-6	6							
A4V-8	8							
A4V-10	10							
A4V-12	12							

The chips are equipped with 2" long bare tinned leads soldered to all anodes and the common cathode.

* 'V' suffix indicates the device is optimized for 'photovoltaic' operation.

* 'C' suffix indicates the device is optimized for 'photoconductive' operation.

* Non-Condensing temperature and Storage Range, Non-Condensing Environment.

** λ = 254 nm